NPN Triple Diffused Planar Silicon Transistor



2SC5777

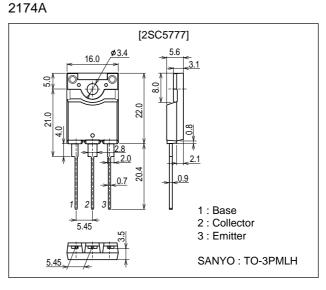
Ultrahigh-Definition CRT Display Horizontal Deflection Output Applications

Features

- High speed.
- High breakdown voltage (VCBO=1600V).
- High reliability (Adoption of HVP process).
- Adoption of MBIT process.
- On-chip damper diode.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		1600	V
Collector-to-Emitter Voltage	VCEO		800	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		10	А
Collector Current (Pulse)	ICP		25	А
Collector Dissipation	Da		3.0	W
	PC	Tc=25°C	80	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =800V, I _E =0			10	μΑ
	ICES	VCE=1600V, RBE=0			1.0	mA
Emitter Cutoff Current	IEBO	V _{EB} =4V, I _C =0	40		200	mA

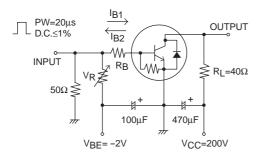
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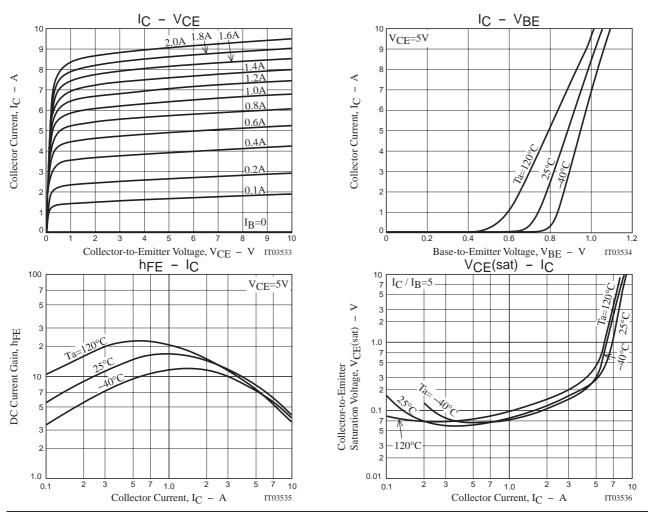
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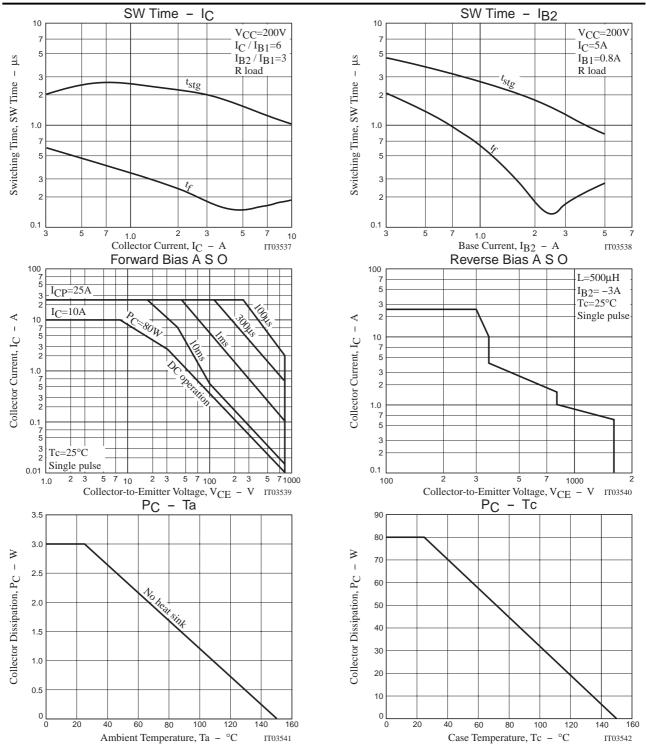
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
DC Current Gain	hFE1	V _{CE} =5V, I _C =1A	8			
	hFE2	V _{CE} =5V, I _C =7A	4		7	
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=6.3A, IB=1.6A			3.0	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=6.3A, IB=1.6A			1.5	V
Storage Time	tstg	IC=5A, IB1=0.8A, IB2=-2.5A			3.0	μs
Fall Time	tf	IC=5A, IB1=0.8A, IB2=-2.5A			0.2	μs
Diode Forward Voltage	٧F	IEC=8A			2.2	V

Switching Time Test Circuit





No.6991-2/4



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